



# Standard Rectifier

$V_{RRM}$	=	800 V
$I_{FAV}$	=	30 A
$V_F$	=	1.25 V

## Single Diode

### Part number

**DSI30-08AS**

Marking on Product: *DSI30-08AS*



Backside: cathode



### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

### Applications:

- Diode for main rectification
- For single and three phase bridge configurations

### Package: TO-263 (D2Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

### Disclaimer Notice

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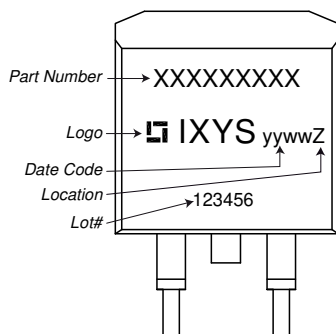
Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					900	V
$V_{RRM}$	max. repetitive reverse blocking voltage					800	V
$I_R$	reverse current	$V_R = 800$ V		$T_{VJ} = 25^\circ\text{C}$		40	$\mu\text{A}$
		$V_R = 800$ V		$T_{VJ} = 150^\circ\text{C}$		1.5	mA
$V_F$	forward voltage drop	$I_F = 30$ A		$T_{VJ} = 25^\circ\text{C}$		1.29	V
		$I_F = 60$ A				1.60	V
		$I_F = 30$ A		$T_{VJ} = 150^\circ\text{C}$		1.25	V
		$I_F = 60$ A				1.66	V
$I_{FAV}$	average forward current	$T_C = 130^\circ\text{C}$		$T_{VJ} = 175^\circ\text{C}$		30	A
		rectangular	d = 0.5				
$V_{FO}$	threshold voltage			$T_{VJ} = 175^\circ\text{C}$		0.82	V
$r_F$	slope resistance					14.1	m $\Omega$
		} for power loss calculation only					
$R_{thJC}$	thermal resistance junction to case					0.9	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.25		K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		160	W
$I_{FSM}$	max. forward surge current	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		300	A
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		325	A
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		255	A
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		275	A
$I^2t$	value for fusing	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		450	A <sup>2</sup> s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		440	A <sup>2</sup> s
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		325	A <sup>2</sup> s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		315	A <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; f = 1 MHz		$T_{VJ} = 25^\circ\text{C}$		10	pF



Package TO-263 (D2Pak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal <sup>1)</sup>			35	A
$T_{VJ}$	virtual junction temperature		-40		175	°C
$T_{op}$	operation temperature		-40		150	°C
$T_{stg}$	storage temperature		-40		150	°C
<b>Weight</b>				1.5		g
$F_C$	mounting force with clip		20		60	N

<sup>1)</sup>  $I_{RMS}$  is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

**Product Marking**



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSI30-08AS-TRL	DSI30-08AS	Tape & Reel	800	489212
Alternative	DSI30-08AS-TUB	DSI30-08AS	Tube	50	470996

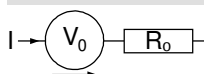
Similar Part	Package	Voltage class
DSI30-08A	TO-220AC (2)	800
DSI30-08AC	ISOPLUS220AC (2)	800
DSI30-12AS	TO-263AB (D2Pak) (2)	1200
DSI30-12A	TO-220AC (2)	1200

DSI30-12AC	ISOPLUS220AC (2)	1200
DSI30-16AS	TO-263AB (D2Pak) (2)	1600
DSI30-16A	TO-220AC (2)	1600

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 175^{\circ}C$



**Rectifier**

$V_{0\ max}$	threshold voltage	0.82	V
$R_{0\ max}$	slope resistance *	11	mΩ

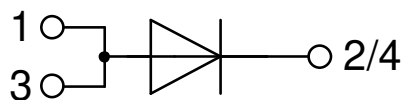


**Outlines TO-263 (D2Pak)**



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
A2	2.41		0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2.5		0.098	
E	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
e	2,54 BSC		0,100 BSC	
e1	4.28		0.169	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

*All dimensions conform with and/or within JEDEC standard.*



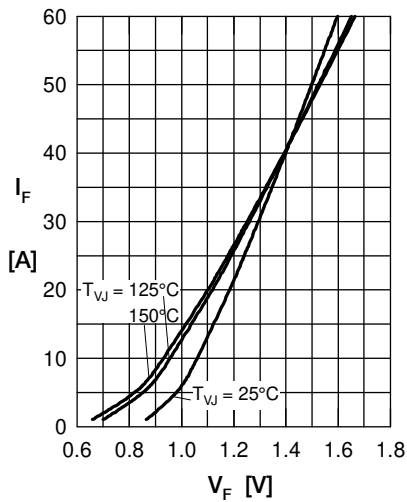
**Rectifier**


Fig. 1 Forward current versus voltage drop per diode

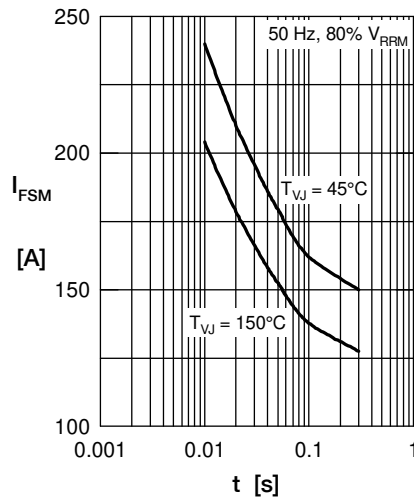


Fig. 2 Surge overload current

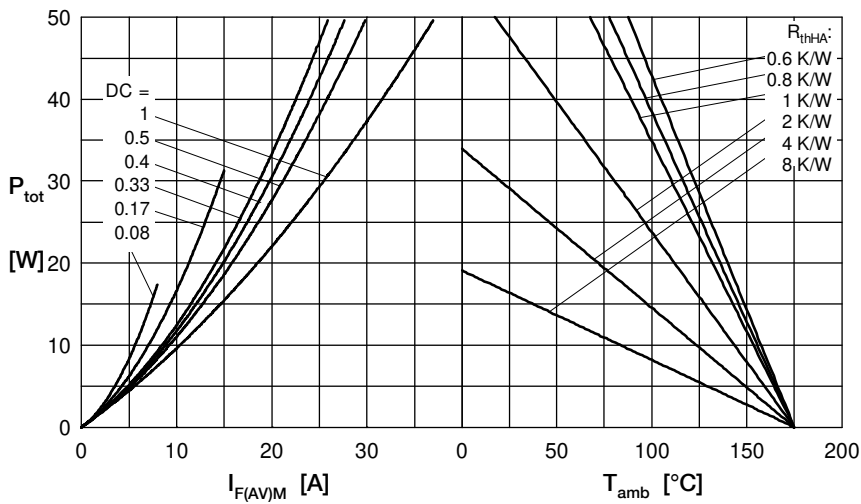

 Fig. 3  $I^2t$  versus time per diode


Fig. 4 Power dissipation vs. direct output current and ambient temperature

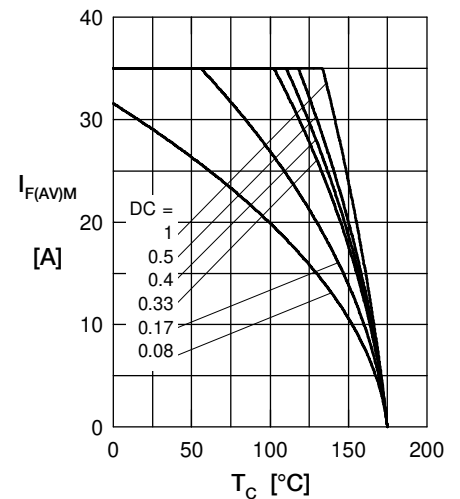


Fig. 5 Max. forward current vs. case temperature

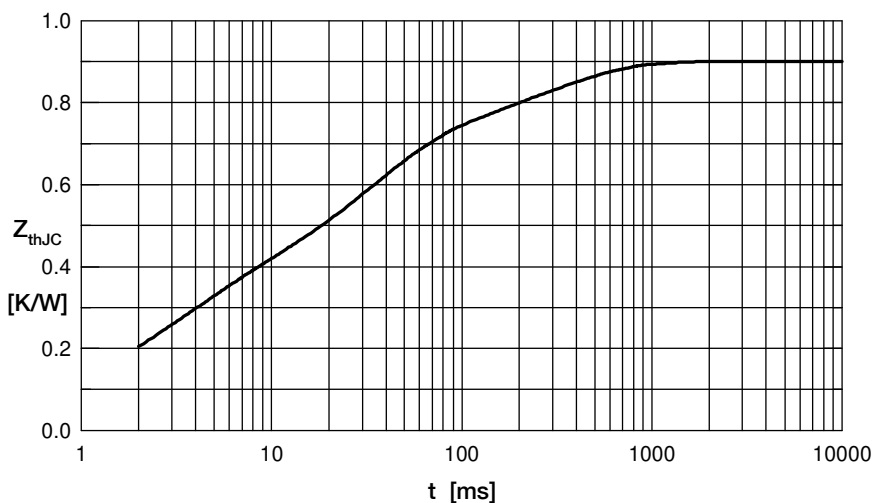


Fig. 6 Transient thermal impedance junction to case

 Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.03	0.0004
2	0.08	0.002
3	0.2	0.003
4	0.39	0.03
5	0.2	0.29